

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

33 A

Features

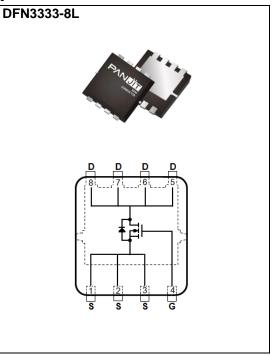
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@16A<17m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@8A<20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	.,,	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C		33	А	
	T _C =100°C	l _D	21		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	132		
Power Dissipation	T _C =25°C	-	48	W	
	Tc=100°C	Pb	24		
Continuous Drain Current(Note 4)	T _A =25°C		7.3		
	T _A =70°C	l _D	5.9	Α	
Power Dissipation	T _A =25°C	-	2.4	W	
	T _A =70°C	Po	1.6		
Single Pulse Avalanche Energy ^(Note 6)		Eas	45	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R ₀ JC	3.1	°C/W	
	Junction to Ambient	R _{θJA}	62.5		

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1	1.7	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =16A	-	13	17	mΩ	
		V _{GS} =4.5V, I _D =8A	-	16	20		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 5)			_				
Total Gate Charge	Q_g	N/ 00\/ L 40A	-	13.5	-	nC	
Gate-Source Charge	Q_gs	V _{DS} =30V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	4.8	-		
Gate-Drain Charge	Q_gd	VGS=4.5 V(1818 2,8)	-	4.9	-		
Input Capacitance	Ciss), OE),), O),	-	1574	-	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	118	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	77	-		
Turn-On Delay Time	td _(on)	\/ 45\/ 40	-	11	-		
Turn-On Rise Time	t _r	V _{DD} =15V, I _D =1A,	-	11	-	ns	
Turn-Off Delay Time	td _(off)	V _{GS} =10V, R _G =6 Ω	-	35	-		
Turn-Off Fall Time	t _f	(14010 2,3)	-	8.1	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	33	А	
Diode Forward Current	Is						
Reverse Recovery Time	V _{SD}	I _S =1A, V _{GS} =0V	-	0.68	1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=30A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

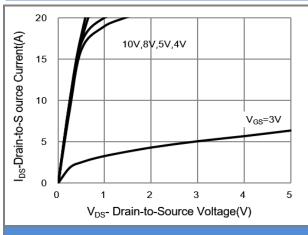


Fig.1 On-Region Characteristics

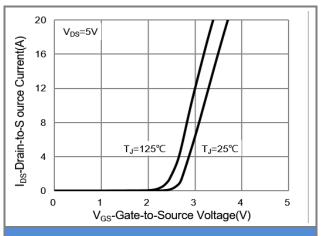


Fig.2 Transfer Characteristics

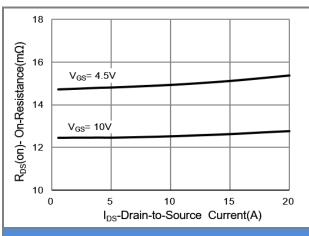


Fig.3 On-Resistance vs. Drain Current

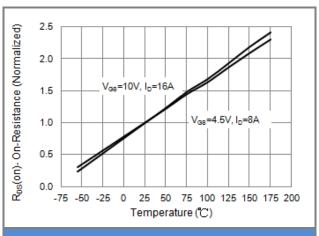


Fig.4 On-Resistance vs. Junction temperature

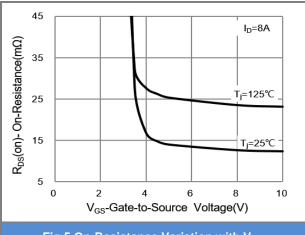


Fig.5 On-Resistance Variation with V_{GS}

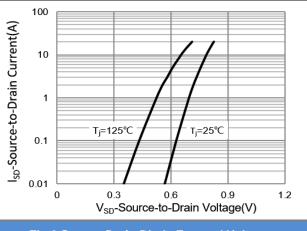


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

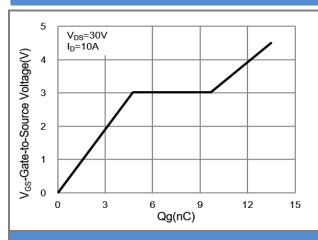


Fig.7 Gate-Charge Characteristics

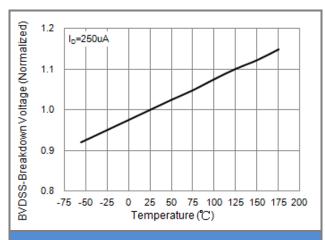


Fig.8 Breakdown Voltage Variation vs. Temperature

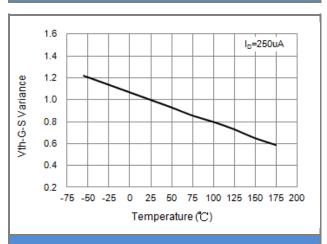


Fig.9 Threshold Voltage Variation with Temperature

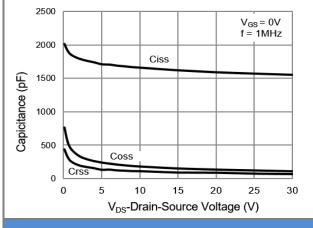
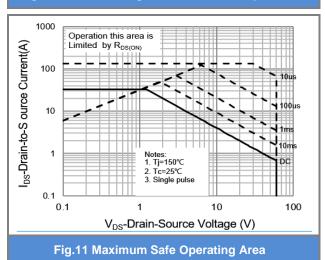


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

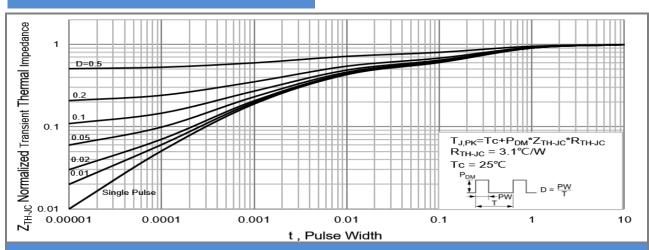


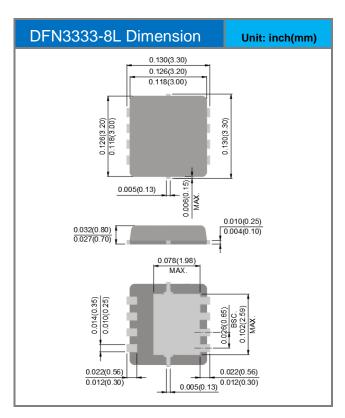
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

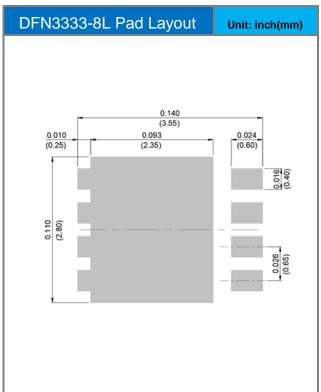


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4464AP-AU	DFN3333-8L	5K pcs / 13" reel	4464

Packaging Information & Mounting Pad Layout







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